E lectronic transport in a series of multiple arbitrary tunnel junctions

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Abstract

M onte Carlo simulations and an analytical approach within the fram ework of a semiclassical model are presented which permit the determination of Coulomb blockade and single electron charging e ects for multiple tunnel junctions coupled in series. The Coulomb gap in the I(V) curves can be expressed as a simple function of the capacitances in the series. Furtherm ore, the magnitude of the di erential conductivity at current onset is calculated in terms of the model. The results are discussed with respect to the number of junctions.

PACS: 73.40 Gk, 73.23 Hk

Keywords: Coulom b blockade, Coulom b staircase, Single electron tunneling, sem iclassical model, multiple tunnel junctions, I-V characteristics

Typeset using REVT_EX

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Since the development of quantum mechanics, electron tunneling has been widely investigated experimentally [1,2] and extensively discussed in theory. [3,4] The rst experiments were performed on metal-insulator-metal (M IM) sandwiches, [1] which permitted the study of tunneling phenomena and the direct correlation of such elects with the thickness of the potential barrier. There are two main theoretical approaches commonly used to describe tunneling phenomena. The rst entails solving the time-independent Schrödinger equation and matching the wave functions. [3] However, an exact matching of the wave functions can only be achieved in a one-dimensional approximation. The second method is known as the transfer-H amiltonian approach, [4] which generally involves a time-dependent Schrödinger equation between the two electrodes is described using a transfer H amiltonian in addition to the H amiltonians of the unperturbed electrodes.

For sm all-scaled system s a particular tunneling phenom enon referred to as single electron tunneling (SET) [5] can occur. SET may be observed, for example, in a system of two electrodes separated by a thin insulating layer, in which a third electrode (e.g., a sm all metal particle) is embedded. The current through the system is controlled by a single electron if $k_B T = e^2 = [2(C_1 + C_2)]$, with C_1 and C_2 being the capacitances of the two junctions. A tunneling event therefore changes the total charge of the center electrode by

e, depending on the direction of tunneling, and thus the electrostatic energy of the system . At zero tem perature, tunneling is completely prohibited for $jV j < e= [2(C_1 + C_2)] = V_{gap} = 2$ (C oulom b blockade), and the transport process is dominated by charging e ects. This means, in particular, that an increase in voltage applied to the double junction system leads to increm ental charging, which m ight manifest itself as steps in the I(V) characteristic (C oulom b staircase). [5] Such I(V) characteristics are usually measured at temperatures below 4 K [7] for certain relations of R_iC_i , such as $R_1C_1 = R_2C_2$ (R_i and C_i are the tunnel resistance and capacitance of the i-th junction). The theory developed so far only considers this low-tem perature lim it.

One important point in understanding SET is the extension of the theory to multiple

tunnel junctions as well as to room temperature. Increasing the temperature to room temperature dem ands capacitances as smallas C ' 0:1 aF, since only then does the electrostatic energy of charging by a single electron, $e^2=2C$, exceed the therm all energy $k_B T$. Now adays, such capacitances can be realized using small particles [7] or clusters [8] with dimensions in the 1 to 10 nm range.

Here, a theoretical study of I(V) characteristics of one-dimensional chains of small capacitors coupled in series is presented. Such arrangements can be realized, for example, in granular lms of small metal islands or with clusters. An analytical approach for zero temperature in the framework of a sem iclassical model is used to explain several features arising in M onte C arb simulations at nite temperatures. It is shown that the width of the C oulom b gap is directly related to the number of capacitors in the series. An expression is given for calculating the voltages at which steps in the I(V) characteristic occur. A dditionally, the dimential conductivity at the current onset just beyond the C oulom b gap is calculated.

Figure 1 shows a system of N tunnel junctions coupled in series. In the semiclassicalmodel, the state of each tunnel junction is characterized by the voltage drop across [Fig. 1 (a)]. The individual junction voltages can be calculated using K inchho 's law together with G auss's law. D us to tunneling there m ight be additional electrons on the center electrodes. The voltage V_k across the k-th junction with n_j extra electrons on the j-th electrode and an externally applied voltage V can be written as

where C_m denotes the capacitance of the m-th tunnel junction. V_k causes a mutual shift in the Ferm i energies of the electrodes.

The tunneling rates across the junctions, which can be calculated using Ferm i's golden rule, are given by the following expression (for tunneling through the k-th junction from right to left):

$$r_{k} = \int_{1}^{Z_{+1}} dE \frac{2}{h} J (E) J D_{k-1} (E E_{k-1}) f (E E_{k-1}) D_{k} (E E_{k}) [I f (E E_{k})]; (2)$$

where f(E) is the Ferm iD irac distribution. If we consider, as usual, the density of states D near the Ferm i level and the tunnel matrix element T to be energy-independent, that is $D_k(E = E_k) = D_k^0$ and $f(E)f = f_0f$, the tunneling rates from right to left (r_k) and reverse (l_k) [cf. Fig.1 (b)] are

$$r_{k} (:::n_{j} :::;V) = \frac{1}{e^{2}R_{k}} \frac{E_{k}}{1 \exp(E_{k} = k_{B}T)}$$
(3)

and

$$l_{k} (:::n_{j}:::;V) = \frac{1}{e^{2}R_{k}} \frac{E_{k}^{!}}{1 \exp(-E_{k}^{!} = k_{B}T)};$$
(4)

where the tunneling resistances R_k are given by $1=R_k = (2 e^2=h) D_{k-1}^0 D_k^0 \mathbf{j}_0 \mathbf{j}_0 \mathbf{j}$. The energy that an electron gains by tunneling through the k-th junction, E_k or $E_k^!$, may be calculated by integrating the di erence between the neighboring Ferm i levels over the tunneling event:

$$\begin{array}{c} & & & & & Z^{1} \\ E_{k} & & & = & e & dq V_{k} (:::;n_{k-1} & q;n_{k} + q;:::;V)) ; \\ E_{k}^{1} & & & & & \\ \end{array}$$
 (5)

This is just the change in the electrostatic energy of the k-th capacitor. Evaluating the integral leads to a simple expression for the energy changes:

$$E_{k}^{(1)} = eV_{k} (:::n_{j}:::;V) \frac{e^{2}}{2} \frac{C_{1}}{C_{k}^{2} (1 + C_{1} \prod_{m=2}^{p} 1 = C_{m})} \frac{e^{2}}{2C_{k}} :$$
 (6)

The I(V) characteristics of this system can be determined numerically by M onte C arb simulation. One main feature of the results which arises in the simulations is a widening of the C oulom b gap with increasing number of tunnel junctions (F ig 2). This can be understood for the zero-temperature limit of the system. A lso, the dimential conductivity at current onset (see inset of F ig 3) can be calculated in this limit. For T = 0, a tunneling event is impossible whenever a tunneling electron would lose energy, that is $E_k < 0$ or $E_k^{!} < 0$, respectively. From any state de ned by the numbers n_j of extra electrons on the center electrodes, the system may undergo a number of transitions by tunneling of an electron somewhere in the series. The energy changes associated with these transitions, E_k and $E_k^{\ l}$, are directly related to the applied voltage via Eq.(6). In the simplest case of only one extra electron in the series (or one extra hole, i.e., the absence of one electron), these energy di erences are negative for zero voltage, i.e., tunneling is in possible. An increasing voltage causes the energies to increase towards and then above zero, thus increasing the number of possible tunneling events. The energy di erences associated with tunneling through the term inating junctions of the chain are the last to become positive. Therefore, the C oulom b gap of multiple junction system s can be determined by examining the voltages at which either $E_1^{\ l}$ and E_1 or $E_N^{\ l}$ and E_N cross zero. For $C_1 < C_N$, the rst tunnel junction is the one that dom inates the process and the C oulom b gap is found to be

$$V_{gap} = e_{i=2}^{X^{N}} \frac{1}{C_{i}}$$
 (7)

For $C_1 > C_N$, the last junction dom inates the process, which means that the sum in Eq.(7) runs from i = 1 to N 1. A similar approach to calculate the size of the C oulom b gap was chosen before, [9] although the system of junctions is not as general as that considered here (the capacitances are taken to be all equal).

H igher threshold voltages can in principle be determ ined in a similar manner, thus accounting for the structure of multiple junction I(V) curves. U sing a fairly simple computer program, one can calculate the states that are accessible from the \ground state", which is given by $n_j = 0$ for all j's, and one can determ ine the threshold voltages at which new states become accessible. A state is accessible if a sequence of tunneling events with nonvanishing probability leads to it. These threshold voltages provide an intuitive understanding of the steps in the I(V) characteristic as well as an exact prediction of the voltages at which they occur. Until now, the step structures in such simulations have usually been presented without explanation or simply been characterized as unusual. [10,11] In the present analysis, how ever, the num ber of predicted threshold voltages exceeds the num ber of steps that occur in the num erical simulation. The occurence of steps depends crucially on the choice of the

resistance values, as will be discussed subsequently.

Just beyond the C oulom b gap, i.e., at voltages slightly above the rst threshold voltage $V_{th} = \frac{1}{2} V_{gap}$, the most probable process is one electron (hole) tunneling through the whole chain of junctions before the next electron (hole) enters. The average time that the electron spends on one particle of the chain is given by the inverse tunneling rate. The average time

to tunnel through the whole chain is therefore

$$= \frac{1}{\frac{1}{l_{N}}(0; \dots; 0; V)} + \frac{1}{\frac{1}{l_{N-1}}(0; \dots; 0; 1; V)} + \dots + \frac{1}{\frac{1}{l_{1}}(1; 0; \dots; 0; V)};$$
(8)

This time is valid for voltages V slightly above the threshold voltage: $V = V_{th} + V$, where V is small. At zero tem perature, the tunneling rates l_k are given by the expression

$$l_{k}(:::n_{j}:::;V) = \begin{cases} \circ & 0 & \text{for } E_{k} < 0; \\ \vdots & E_{k} = (e^{2}R_{k}) & \text{for } E_{k} & 0: \end{cases}$$
(9)

Therefore, just above the threshold voltage $V_{\rm th}$, the voltage at which the energy change at the N th junction,

$$E_{N}^{!} = \frac{e}{C_{N} \prod_{m=1}^{N} 1 = C_{m}} V;$$

crosses zero, the rst term in Eq.(8) dom in a tes. The I (V) dependence near $V_{\rm th}$ is thus given by

$$I(V) = \frac{e}{e} = e \frac{1}{N} (0; :::; 0; V)$$

$$= \begin{cases} 8 \\ \gtrless & 0 & \text{for } V < V_{\text{th}}; \\ \frac{e}{N} & 1 = C_{\text{m}} \end{cases} \text{ for } V \text{ for } V \text{ V_{th}};$$

$$(10)$$

In the inset of F ig.3, M onte C arb results obtained close to the set threshold voltage are shown for two sets of parameters and are compared with the asymptotes given by Eq.(10). This gure demonstrates how drastically the dimensional conductivities at current onset, given the same average slope of $1 = \frac{P_{i=1}^{N} R_{i}}{i=1} R_{i}$, depend on the value of the resistance of junction 1, which in this case determines the threshold voltage. It also shows the good agreement of the numerical data with the analytical result.

In a more rigorous approach, probabilities $P(:::n_j:::)$ must be assgined to the states (:::n_j:::) of the system. These probabilities must be solutions of the stationary master equation of the system. The correct expansion for the stationary current is then given by

$$I = e P (:::n_{j}:::) [I_{N} (:::n_{j}:::;V) K_{N} (:::n_{j}:::;V)];$$
(11)

sum m ing over all possible electronic states $(:::n_j:::)$ of the system with an arbitrary num ber of extra electrons on the center electrodes.

For voltages $V = V_{th} + V$ near the nst threshold voltage, the probability of the \ground state" (0;:::;0) is alm ost 1, i.e., P (0;:::;0) ' 1, and the probabilities of all other states are negligible. This results from the fact that, while the transition rates from the state (0;:::;0) to neighboring states are zero or nearly zero, the transition rates back to the ground state are already nite. Furtherm ore, r_N (0;:::;0;V) vanishes for positive voltages V, leaving only l_N (0;:::;0;V). Therefore Eq.(11) reduces to

$$I = e \downarrow (0; ...; 0; V)$$
 (12)

near the rst threshold voltage, which is the same result as obtained above in Eq.(10).

It is, of course, quite di cult to calculate analytically the probabilities of the states from the full master equation of the system, although it is possible (for capacitances all equal) to write an analytical expression for the average current without an explicit solution of the master equation in the case when the voltage corresponds to the rst two steps in the I(V) characteristic. [12] Qualitatively, one can expect | as at the rst threshold voltage | the steepest steps in I(V) to occur when tunneling through the junction with the lowest resistance value creates access to a new state. Higher steps may only occur when the associated threshold voltage is determined by a junction k_0 for which

$$(C_{k_0} R_{k_0} \prod_{m=1}^{N} 1 = C_m)^{-1} \qquad \frac{1}{\mathbb{P}} R_i$$

This tendency can also be seen in the results of Fig.3. The solid arrows indicate voltages at which new states become accessible by tunneling through junction 1, which manifests itself as steps in the (thicker) I(V) curve for parameter set 1 (R_1 sm all). At voltages indicated by the dashed arrows, new states become accessible by tunneling through the last junction 6, corresponding to steps in the (thinner) curve for parameter set 2 (R_6 sm all).

In conclusion, M onte C arb simulations of I(V) characteristics in a one-dimensional arrangement of tunnel junctions as well as an analytical approach have been presented. The analytical results m ay be used to understand the features found in the simulations. The results are in general useful for the qualitative and quantitative understanding of experimental I(V) curves. The voltages at which steps occur can be predicted using the presented form alism | in particular, the size of the C oulom b gap can be determined. E orts are currently in progress to extend the theoretical approach to nite temperatures and to investigate in m ore detail the in uence of certain system parameters, such as the resistance values in the junction array, on the resulting I(V) curves.

ACKNOW LEDGM ENTS

This work was supported by BM BF (G rant: 13N 6562).

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FIGURES

FIG.1. (a) C incuit diagram of a system of N tunnel junctions in series, represented by their capacitances C_i . The voltage drop across the i-th tunnel junction is V_i . (b) Schem atic diagram of the tunnel junctions coupled in series, showing the various tunneling rates l_i , r_i .

FIG.2. M onte C arlo simulations of I (V) curves for (a) 3, (b) 5 and (c) 10 tunnel junctions. The parameters for the simulations are $C_1 = 12 \text{ aF}$, $C_2 = C_N_1 = 1.4 \text{ aF}$, $C_N = 2.8 \text{ aF}$ and $R_1 = 0.01 \text{ M}$, $R_2 = R_N_1 = 280 \text{ M}$, $R_N = 2.8 \text{ M}$ and T = 4.2 K.

FIG.3. M onte Carlo sinulation and analytical predictions for the I(V) step structure of a 6-junction system. The parameters are T = 0.01K, $C_1 = 1.2 \text{ aF}$, $C_{2:::5} = 2.8 \text{ aF}$, $C_1 = 4.4 \text{ aF}$ (in both cases), $R_1 = 24M$, $R_{2:::5} = 560M$, $R_6 = 8000M$ (thick line, set 1) and $R_1 = 8000M$, $R_{2:::5} = 560M$, $R_6 = 24M$ (thin line, set 2). Solid arrows indicate access through junction 1, dashed arrows through junction 6 (see text). In the inset, current onsets for the two sets of parameters are magnied. The diamonds (set 1) and squares (set 2) are Monte Carlo results, whereas the solid lines display the asymptotes for V ! V_{th} from the analytical expression. The dot-dashed line shows the average slope for reference.

Fig.1: U.E.Volmar et al., Electronic transport in a series ...



Fig.2: U.E.Volmar et al., Electronic transport in a series ...



Fig.3: U.E.Volmar et al., Electronic transport in a series ...



current (nA)